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metallization layer 5 - the drain contact of the semiconductor switch 17 - the source contact of the semiconductor switch 17 - the bonding connection 16, the metallization layer 5 - the drain contact of the semiconductor switch 17' - the source contact of the semiconductor switch 17' - the lead 9 - the load current connection element 10, connected to the first supply potential 11 (reference-ground potential).

In the Claims:

12

Claim 3 (amended). The semiconductor component according to claim 1, wherein each of said two switching elements contain two semiconductor switches connected in series, each of said two semiconductor switches is connected to one of said external load current connection elements and forms an output of the semiconductor component.